Notice of Allowability	Application No.	Applicant(s)	
	09/787,189	SLATER JR., DAVID B	
	Examin r	Art Unit	<u> </u>
	DAVID VIII	2010	
	DAVID VU	2818	
The MAILING DATE of this communication appears on the cover she t with the correspondence address Il claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included erewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS OTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative f the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.			
 This communication is responsive to 10/15/03. The allowed claim(s) is/are 1-7. The drawings filed on 15 March 2001 are accepted by the Acknowledgment is made of a claim for foreign priority under the communication of the communication is responsive to 10/15/03. 			
a) All b) Some* c) None of the:			
1. Certified copies of the priority documents have been received.			
2. Certified copies of the priority documents have been received in Application No			
3. Copies of the certified copies of the priority documents have been received in this national stage application from the			
International Bureau (PCT Rule 17.2(a)). * Certified copies not received:			
5. Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application) since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78.			
(a) The translation of the foreign language provisional application has been received.			
6. Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121 since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78.			
Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted pelow. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.			
7. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.			
 B. ☐ CORRECTED DRAWINGS (as "replacement sheets") mus (a) ☐ including changes required by the Notice of Draftspers 1) ☐ hereto or 2) ☐ to Paper No 		948) attached	
(b) including changes required by the proposed drawing correction filed, which has been approved by the Examiner.			
(c) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No			
Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in t			back) of
9. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT FOR T			Note the
Attachment(s)			
1⊠ Notice of References Cited (PTO-892)	5∏ Notice of Informal Pa	tent Application (PTO	-152)
2 Notice of Draftperson's Patent Drawing Review (PTO-948)	6⊡ Interview Summary (F	PTO-413), Paper No	·
3 Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No. 02/11/02	i), 7□ Examiner's Amendme	ent/Comment	
4 Examiner's Comment Regarding Requirement for Deposit of Biological Material	8⊠ Examiner's Statemen	t of Reasons for Allow	vance
	(H)		
David Nelms			
Supervisory Patent Examiner			
Technology Center 2800			

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DETAILED ACTION

Election/Restrictions

1. This application is in condition for allowance except for the presence of claims 8-20 nonelected without traverse. Accordingly, claims 8-20 have been cancelled.

2. Cancel claims 8-20.

Reason for allowance

3. The following is an examiner's statement of reason for allowance: None of the references of record teaches or suggests a method for forming an ohmic contact to silicon carbide for a semiconductor device, the method comprising: the epitaxial layer is gown on the surface of the silicon carbide substrate after the implanted phosphorus has been annealed and on the surface of the silicon carbide substrate that is opposite to the implanted surface then the last step is the deposition of the metal layer on the implanted surface of the annealed silicon carbide to thus form the ohmic contact.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance".

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Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to David Vu whose telephone number is 571-272-1798. The examiner can normally be reached on Monday-Friday 8:00am-5:30pm. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on 571-272-1787. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7722 for After Final communications. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

DV

David Vu.

Bavid Nelms

Supervisory Patent Examiner Technology Center 2800